

Form PTO-1449
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Patent and Trademark Office

Atty D cket 0756-2345

Serial No. N/A

INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: July 31, 2001

Group Art Unit

J0819 U.S. PTO
02/15/2001

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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Examiner

Date Considered

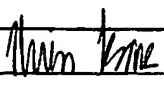
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INFORMATION DISCLOSURE STATEMENT				Applicants: Shunpei YAMAZAKI et al.			
				Filing Date: July 31, 2001		Group Art Unit: 2811	
FOREIGN PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No	
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Examiner <i>Thomson</i>				Date Considered 02-20-04			
<p>*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	09/917,633
				Filing Date	July 31, 2001
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2811
				Examiner Name	
Sign _____ of _____				Attorney Docket Number	740756-2345

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.

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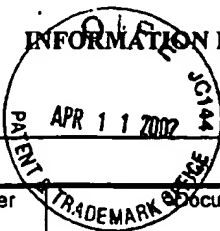
Serial No. 09/917,633

INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: July 31, 2001

Group Art Unit: 2811



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				Filing Date	July 31, 2001
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				Group Art Unit	2811
				Examiner Name	
Sheet 1 of 1	Attorney Docket Number		740756-2345		

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
TT		5,595,944		Zhang et al.	01/21/1997	
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